TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

2SK118

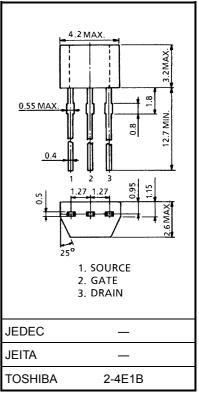
General Purpose and Impedance Converter and Condenser Microphone Applications

- High breakdown voltage: $V_{GDS} = -50 \text{ V}$
- High input impedance: $I_{GSS} = -1 \text{ nA (max) (V}_{GS} = -30 \text{ V)}$
- Low noise: NF = 0.5dB (typ.) (RG = $100 \text{ k}\Omega$, f = 120 Hz)
- Small package

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	V_{GDS}	-50	٧
Gate current	IG	10	mA
Drain power dissipation	P _D	100	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

Unit: mm



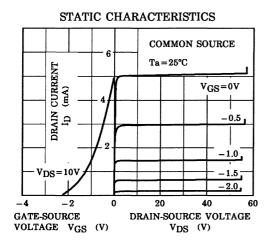
Weight: 0.13 g (typ.)

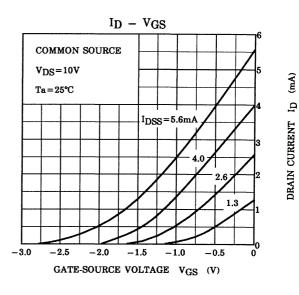
Electrical Characteristics (Ta = 25°C)

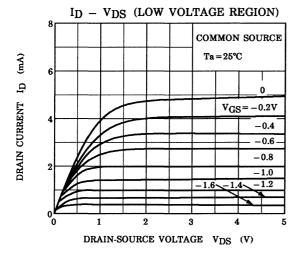
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate cut-off current	I _{GSS}	$V_{GS} = -30 \text{ V}, V_{DS} = 0$	_	_	-1.0	nA
Gate-drain breakdown voltage	V (BR) GDS	$V_{DS} = 0$, $I_G = -100 \mu A$	-50	_	_	V
Drain current	I _{DSS} (Note)	V _{DS} = 10 V, V _{GS} = 0	0.3	_	6.5	mA
Gate-source cut-off voltage	V _{GS (OFF)}	$V_{DS} = 10 \text{ V}, I_D = 0.1 \mu A$	-0.4	_	-5.0	V
Forward transfer admittance	Y _{fs}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ kHz}$	1.2	_	_	mS
Input capacitance	C _{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	_	8.2	_	pF
Reverse transfer capacitance	C _{rss}	$V_{GD} = -10 \text{ V}, I_D = 0, f = 1 \text{ MHz}$	_	2.6	_	pF
Noise figure	NF	V_{DS} = 15 V, V_{GS} = 0, R_G = 100 k Ω , f = 120 Hz		0.5	5.0	dB

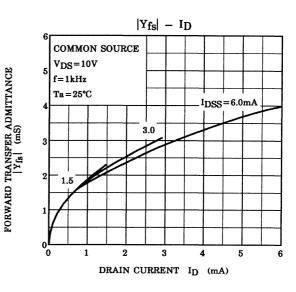
Note: IDSS classification R: $0.3\sim0.75$ mA, O: $0.6\sim1.4$ mA, Y: $1.2\sim3.0$ mA, GR: $2.6\sim6.5$ mA

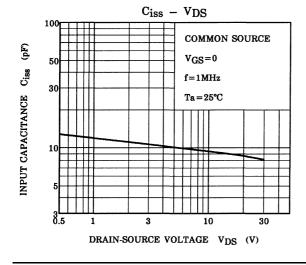
(mA)

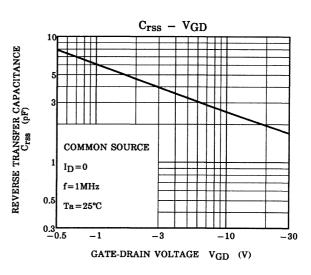




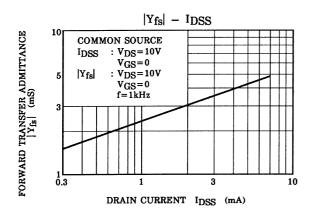


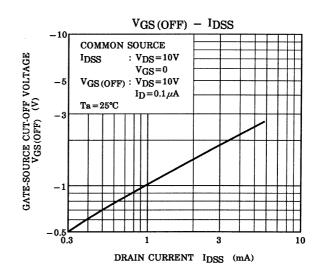


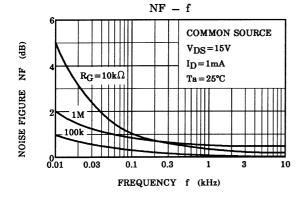


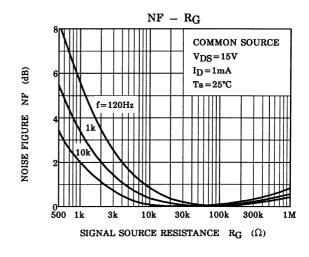


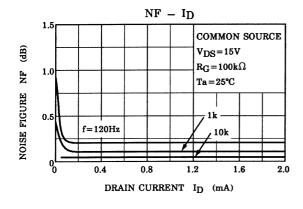
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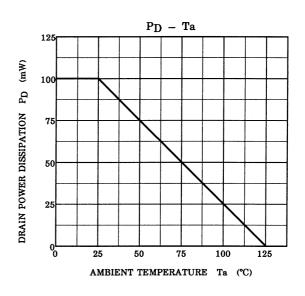


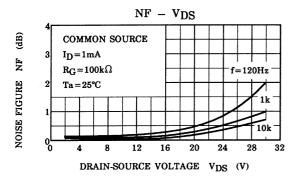












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